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ON Semiconductor®

## FDD8447L-F085

### N-Channel PowerTrench® MOSFET

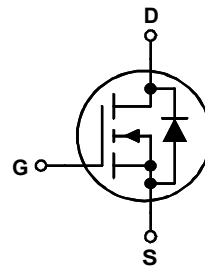
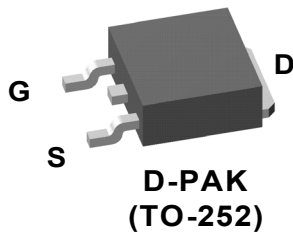
40V, 50A, 11.0mΩ

#### Features

- Typ  $r_{DS(on)}$  = 7.0mΩ at  $V_{GS} = 10V$ ,  $I_D = 14A$
- Typ  $r_{DS(on)}$  = 8.5mΩ at  $V_{GS} = 4.5V$ ,  $I_D = 11A$
- Fast Switching
- Qualified to AEC Q101
- RoHS Compliant

#### Applications

- Inverter
- Power Supplies
- Automotive Engine Control
- Power Train Management
- Solenoid and Motor Drivers
- Electronic Transmission
- Primary Switch for 12V and 24V Systems



## MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Ratings	Units
$V_{DSS}$	Drain to Source Voltage	(Note 1)	40	V
$V_{GS}$	Gate to Source Voltage		$\pm 20$	V
$I_D$	Drain Current Continuous ( $T_C < 80^\circ\text{C}$ , $V_{GS} = 10\text{V}$ )		50	A
	Pulsed		See Figure 4	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 2)	40	mJ
$P_D$	Power Dissipation		65	W
	Dereate above $25^\circ\text{C}$		0.43	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature		-55 to + 175	$^\circ\text{C}$

## Thermal Characteristics

Symbol	Parameter	Test Conditions	Ratings	Units
$R_{\theta JC}$	Maximum Thermal Resistance Junction to Case		2.3	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-252, 1in <sup>2</sup> copper pad area		40	$^\circ\text{C/W}$

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8447L	FDD8447L-F085	D-PAK(TO-252)	13"	12mm	2500 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$B_{VDSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	40	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

### On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	1.0	1.9	3.0	V
$r_{DS(on)}$	Drain to Source On Resistance	$I_D = 14\text{A}$ , $V_{GS} = 10\text{V}$	-	7.0	8.5	m $\Omega$
		$I_D = 11\text{A}$ , $V_{GS} = 4.5\text{V}$	-	8.5	11.0	
		$I_D = 14\text{A}$ , $V_{GS} = 10\text{V}$ , $T_J = 125^\circ\text{C}$	-	10.4	14.0	
$g_{FS}$	Forward Transconductance	$I_D = 14\text{A}$ , $V_{DS} = 5\text{V}$	-	58	-	S

### Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units	
$C_{iss}$	Input Capacitance	$V_{DS} = 20\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$	-	1970	-	pF	
$C_{oss}$	Output Capacitance		-	250	-	pF	
$C_{rss}$	Reverse Transfer Capacitance		-	150	-	pF	
$R_g$	Gate Resistance	$f = 1\text{MHz}$	-	1.27	-	$\Omega$	
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	$V_{DD} = 20\text{V}$ $I_D = 14\text{A}$ $V_{GS} = 10\text{V}$	-	37	52	nC
$Q_{g(5)}$	Total Gate Charge at 5V	$V_{GS} = 0$ to 5V		-	20	28	nC
$Q_{gs}$	Gate to Source Gate Charge			-	6	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			-	7	-	nC

**Electrical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Switching Characteristics**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 20\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$	-	12	21	ns
$t_r$	Rise Time		-	12	21	ns
$t_{d(off)}$	Turn-Off Delay Time		-	38	61	ns
$t_f$	Fall Time		-	9	18	ns

**Drain-Source Diode Characteristics**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{SD}$	Source to Drain Diode Voltage	$I_{SD} = 14\text{ A}$	-	0.8	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 14\text{ A}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}$	-	22	29	ns
$Q_{rr}$	Reverse Recovery Charge		-	11	14	nC

**Notes:**

- 1: Starting  $T_J = 25^\circ\text{C}$  to  $175^\circ\text{C}$ .
- 2: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.05\text{ mH}$ ,  $I_{AS} = 40\text{ A}$

### Typical Characteristics

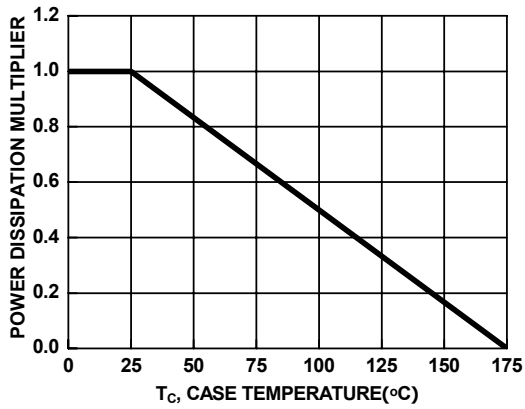


Figure 1. Normalized Power Dissipation vs Case Temperature

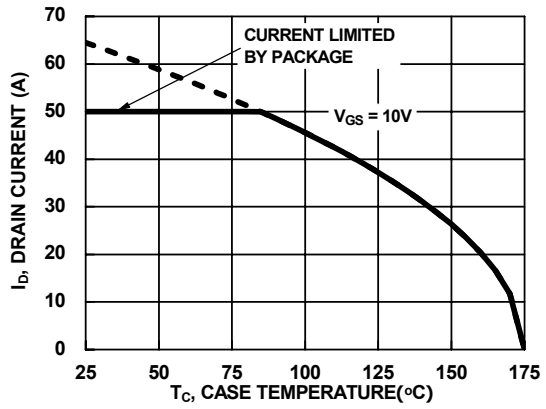


Figure 2. Maximum Continuous Drain Current vs Case Temperature

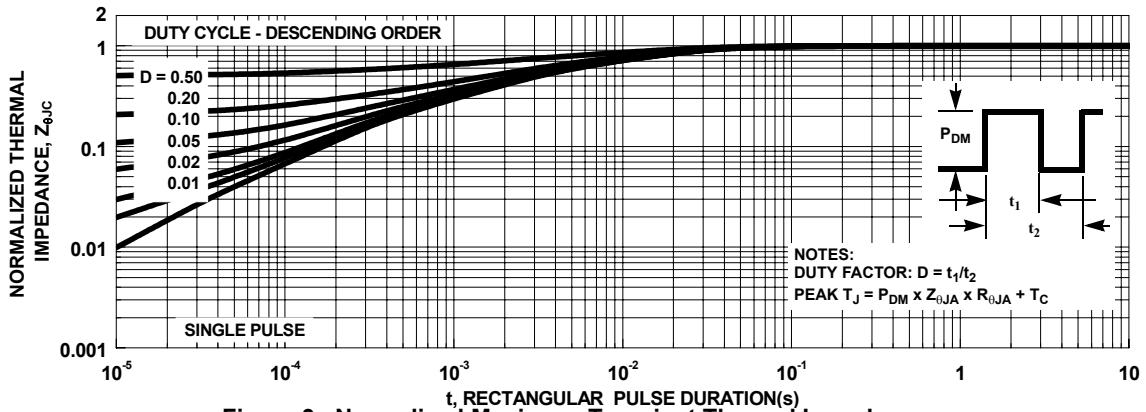


Figure 3. Normalized Maximum Transient Thermal Impedance

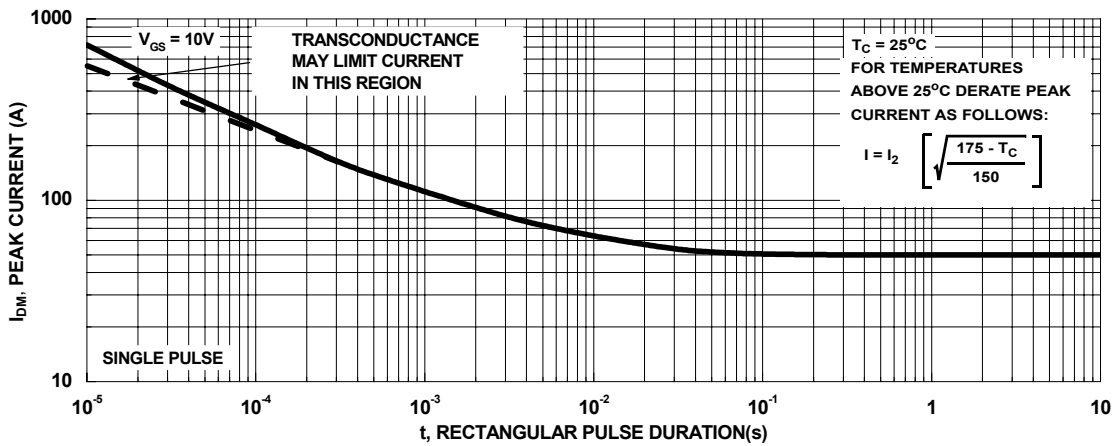


Figure 4. Peak Current Capability

## Typical Characteristics

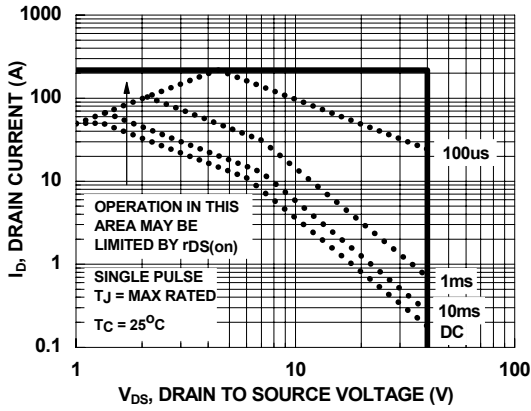


Figure 5. Forward Bias Safe Operating Area

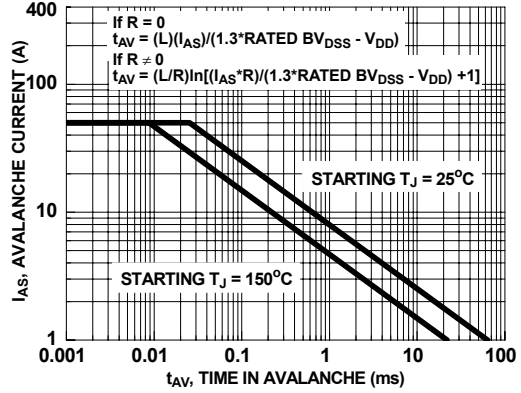


Figure 6. Unclamped Inductive Switching Capability

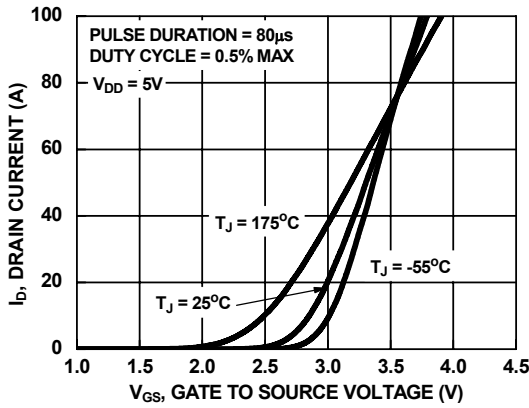


Figure 7. Transfer Characteristics

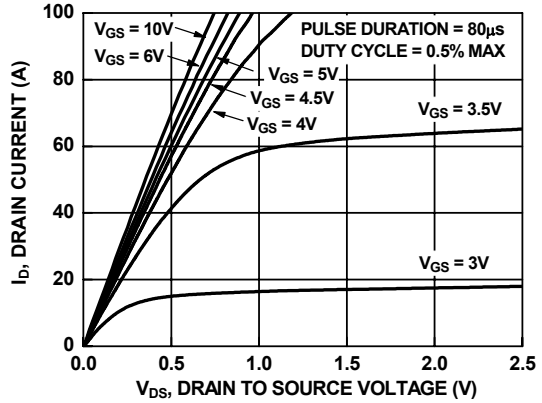


Figure 8. Saturation Characteristics

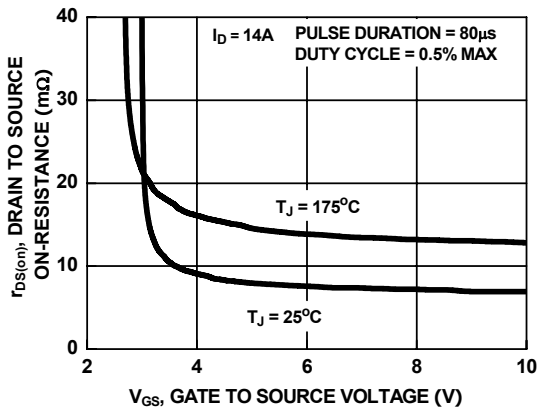


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

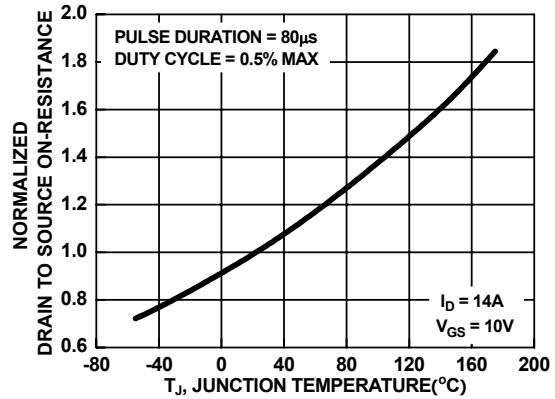


Figure 10. Normalized Drain to Source On-Resistance vs Junction Temperature

### Typical Characteristics

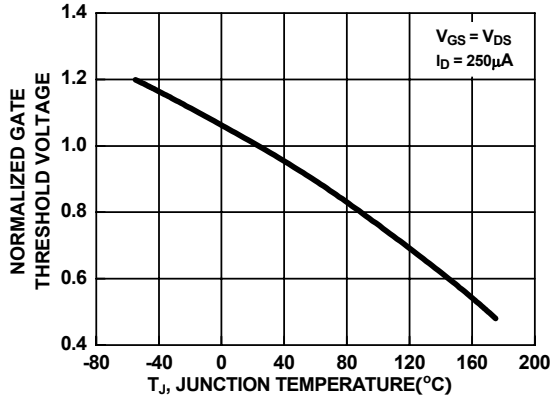


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

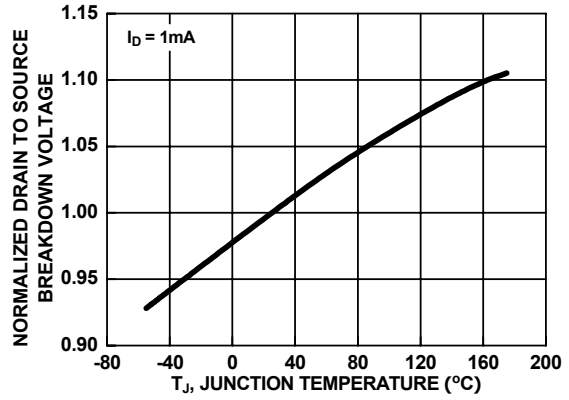


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

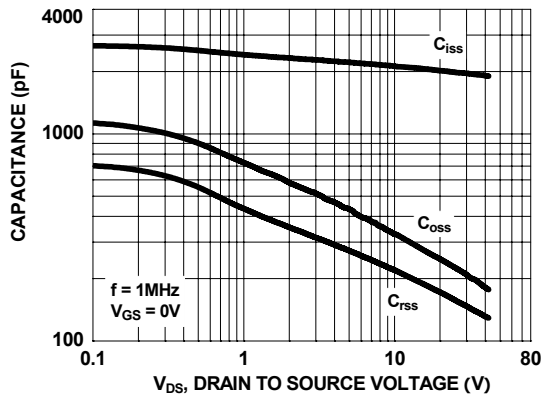


Figure 13. Capacitance vs Drain to Source Voltage

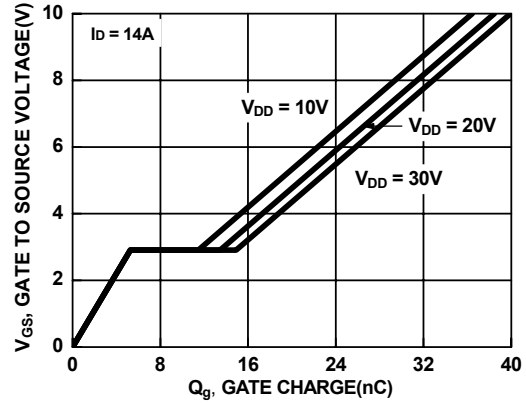


Figure 14. Gate Charge vs Gate to Source Voltage

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